

Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE

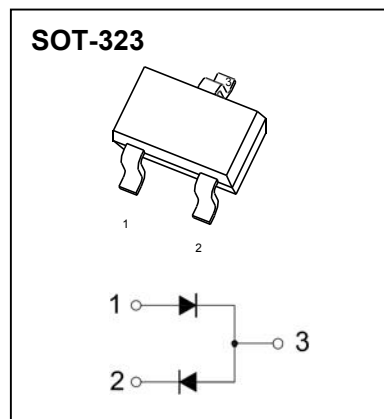
FEATURES

- Small Package
- Low Forward Voltage

APPLICATIONS

- High Speed Switching

MARKING: ME



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	DC Blocking Voltage	10	V
I_o	Forward Continuous Current	100	mA
I_{FM}	Peak Forward Current	200	mA
I_{FSM}	Non-respetitive Peak Forward Surge Current@t=8.3ms	1	A
P_D	Power Dissipation	100	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	1000	$^{\circ}\text{C}/\text{W}$
T_j	Operating Junction Temperature Range	-40 ~ +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	10			V
Reverse current	I_R	$V_R=10\text{V}$			20	μA
Forward voltage	V_F	$I_F=1\text{mA}$		0.18		V
		$I_F=5\text{mA}$			0.3	
		$I_F=100\text{mA}$			0.5	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			40	pF



CHINA BASE
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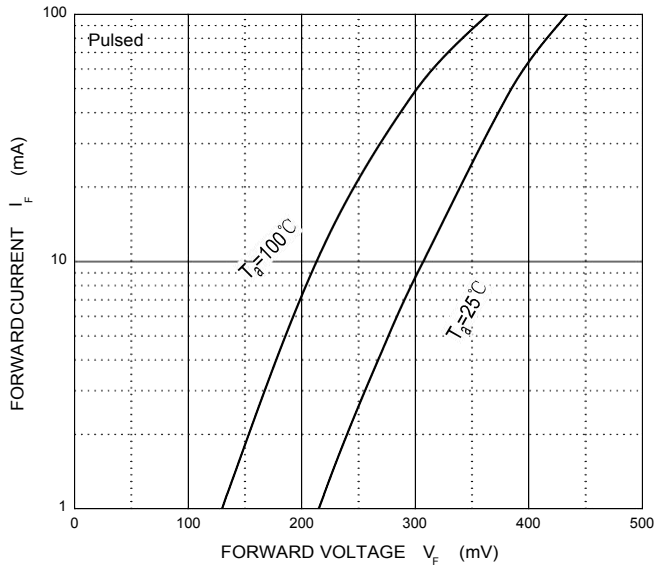
SOT-323 1SS372W



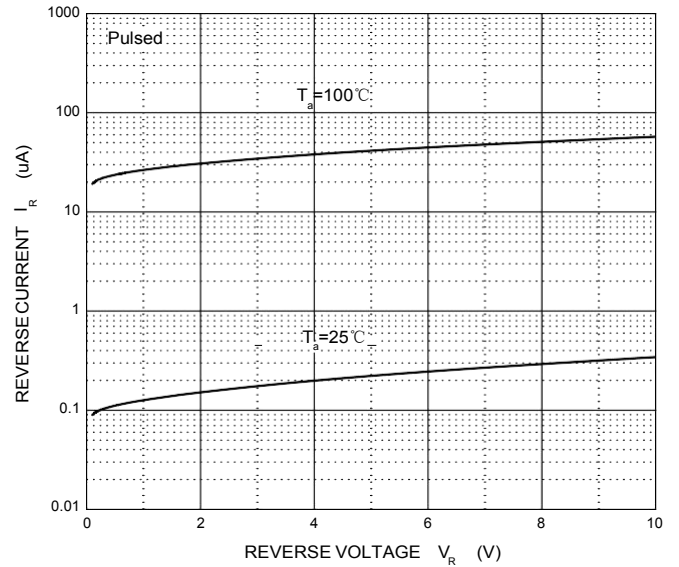
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Typical Characteristics

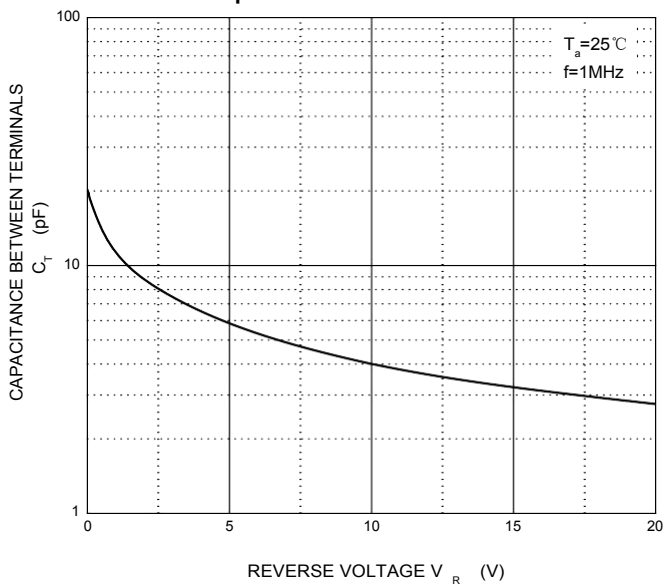
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

